

# SANYO Semiconductors

DATA SHEET

# SFT1403 — General-Purpose Switching Device Applications

#### Features

- Motor drive application.
- Low ON-resistance.
- 4V drive.

## **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

| Parameter                   | Symbol | Conditions             | Ratings     | Unit |
|-----------------------------|--------|------------------------|-------------|------|
| Drain-to-Source Voltage     | VDSS   |                        | 35          | V    |
| Gate-to-Source Voltage      | VGSS   |                        | ±20         | V    |
| Drain Current (DC)          | ۱D     |                        | 14          | А    |
| Drain Current (PW≤10μs)     | IDP    | PW≤10µs, duty cycle≤1% | 56          | А    |
| Allowable Power Dissipation | D-     |                        | 1.0         | W    |
|                             | PD     | Tc=25°C                | 20          | W    |
| Channel Temperature         | Tch    |                        | 150         | °C   |
| Storage Temperature         | Tstg   |                        | -55 to +150 | °C   |

#### Electrical Characteristics at Ta=25°C

| Parameter                                  | Symbol                | Conditions                                | Ratings |     |       | 1.114        |
|--|-----------------------|---|---------|-----|-------|--------------|
|  |                       |   | min     | typ | max   | Unit         |
| Drain-to-Source Breakdown Voltage          | V(BR)DSS              | ID=1mA, VGS=0V                            | 35      |     |       | V            |
| Zero-Gate Voltage Drain Current            | IDSS                  | V <sub>DS</sub> =35V, V <sub>GS</sub> =0V |         |     | 1     | μΑ           |
| Gate-to-Source Leakage Current             | IGSS                  | VGS=±16V, VDS=0V                          |         |     | ±10   | μA           |
| Cutoff Voltage                             | VGS(off)              | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA | 1.2     |     | 2.6   | V            |
| Forward Transfer Admittance                | yfs                   | V <sub>DS</sub> =10V, I <sub>D</sub> =7A  | 6.6     | 11  |       | S            |
| Static Drain-to-Source On-State Resistance | RDS(on)1              | ID=7A, VGS=10V                            |         | 17  | 23    | mΩ           |
|  | R <sub>DS</sub> (on)2 | ID=7A, VGS=4V                             |         | 25  | 35    | mΩ           |
|  | RDS(on)2              | I <sub>D</sub> =7A, V <sub>GS</sub> =4V   |         | -   | ontir | 35<br>wed or |

Marking : T1403

- Continued on next page.
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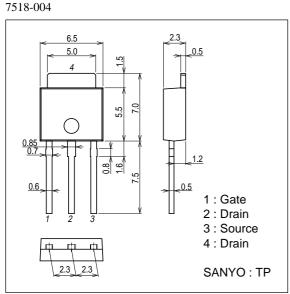
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| Continued from preceding page. |                     |   |     | www.    | DataShe | et4U.cor |
|--------------------------------|---------------------|---|-----|---------|---------|----------|
| Parameter                      | Symbol              | Conditions  |     | Ratings |         |          |
|                                |                     |   | min | typ     | max     | Unit     |
| Input Capacitance              | Ciss                | VDS=20V, f=1MHz   |     | 2230    |         | pF       |
| Output Capacitance             | Coss                | V <sub>DS</sub> =20V, f=1MHz                                    |     | 305     |         | pF       |
| Reverse Transfer Capacitance   | Crss                | VDS=20V, f=1MHz   |     | 225     |         | pF       |
| Turn-ON Delay Time             | t <sub>d</sub> (on) | See specified Test Circuit.                                     |     | 21      |         | ns       |
| Rise Time                      | tr                  | See specified Test Circuit.                                     |     | 110     |         | ns       |
| Turn-OFF Delay Time            | td(off)             | See specified Test Circuit.                                     |     | 140     |         | ns       |
| Fall Time                      | tf                  | See specified Test Circuit.                                     |     | 100     |         | ns       |
| Total Gate Charge              | Qg                  | V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =14A |     | 39      |         | nC       |
| Gate-to-Source Charge          | Qgs                 | VDS=20V, VGS=10V, ID=14A  |     | 7.7     |         | nC       |
| Gate-to-Drain "Miller" Charge  | Qgd                 | V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =14A |     | 7.2     |         | nC       |
| Diode Forward Voltage          | VSD                 | IS=14A, VGS=0V  |     | 0.92    | 1.2     | V        |

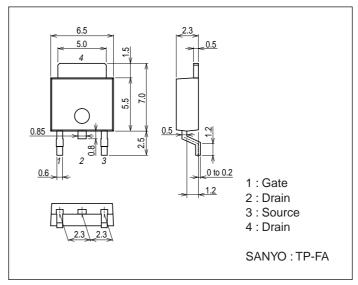
#### **Package Dimensions**

unit : mm (typ)

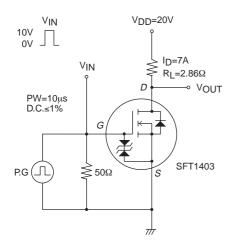


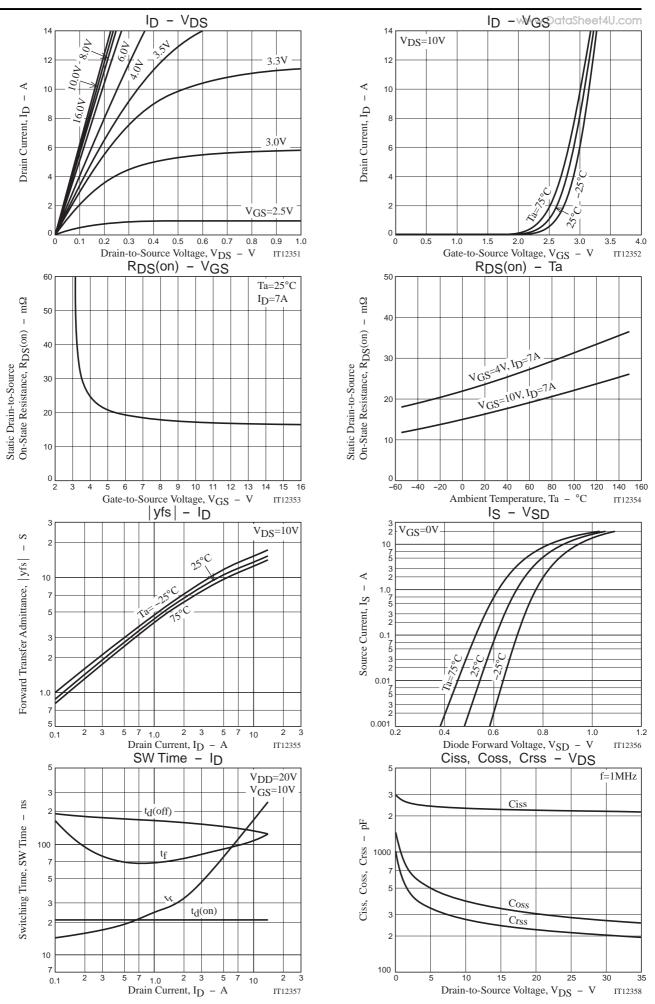
#### **Package Dimensions**

unit : mm(typ) 7003-004

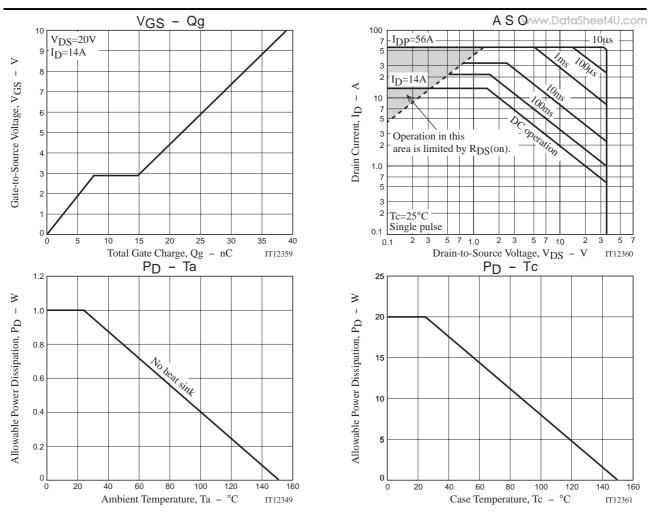


### **Switching Time Test Circuit**





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Note on usage : Since the SFT1403 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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